

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE CLAIMS:**

Claims 16 and 17 have been added.

Claim 13 has been amended as follows:

1        13. (Twice Amended) A semiconductor device having a semiconductor chip,  
2        first electrodes formed on said semiconductor chip,  
3        barrier metals formed on said first electrodes and having laminated structures, and  
4        a plurality of second protruded electrodes, which serve as external connection terminals,  
5        formed on said barrier metals, wherein said barrier metals comprising:  
6                a lowermost conductive metal layer laminated on said first electrodes, said lowermost  
7        conductive metal layer having a comparatively good joining property with said first electrodes;  
8                an intermediate conductive metal layer laminated on said lowermost conductive metal  
9        layer, said intermediate conductive metal layer comprising one or more layers and having a  
10      comparatively good joining property with said lowermost conductive metal layer, said intermediate  
11      conductive metal layer having at least one layer serving as a barrier layer for preventing said  
12      protruded electrodes from diffusing into said intermediate conductive metal layer; and  
13                an uppermost conductive metal layer laminated on said one or more intermediate  
14      conductive metal layers, said uppermost conductive metal layer being made of a material which  
15      easily alloys with the material of said intermediate conductive metal layers and which has good  
16      resistance to oxidation.